

1N5809

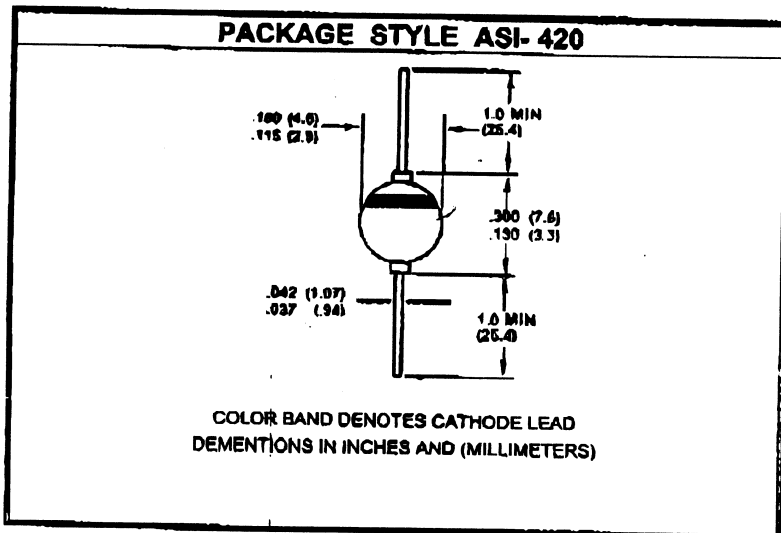
SILICON RECTIFIER-VERY FAST SWITCHING

DESCRIPTION:

The 1N5809 is Designed for General Purpose Very Fast Switching Applications.

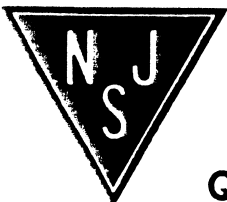
MAXIMUM RATINGS

I_O	$I_F = 6.0 \text{ A (AVG)} @ T_L = 75^\circ\text{C} / L = 3/8''$
V_{RWM}	100 V
T_J	$-65^\circ\text{C to } +175^\circ\text{C}$
T_{STG}	$-65^\circ\text{C to } +175^\circ\text{C}$
θ_{JC}	18°C/W



CHARACTERISTICS $T_c = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_R	$V_R = 100 \text{ V}$ $T_J = 100^\circ\text{C}$			5.0	μA
V_F	$I_F = 4.0 \text{ A}$			0.875	V
C_J	$V_R = 4.0 \text{ V}$ $f = 1.0 \text{ MHz}$		65		
t_{FSM}	$I_F = 1.0 \text{ A}$ $I_R = 1.0 \text{ A}$ (Non repetitive) $t = 8.3 \text{ mS}$ $I_{REC} = 0.1 \text{ A}$		15	90	μS , A
				125	A



Quality Semi-Conductors